



BC846A - BC848C

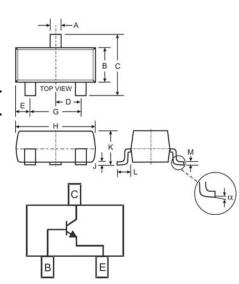
NPN SURFACE MOUNT SMALL SIGNAL TRANSISTOR

Features

- Ideally Suited for Automatic Insertion
- Complementary PNP Types Available (BC856-BC858)
- For Switching and AF Amplifier Applications
- Lead Free/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Pin Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Approximate Weight: 0.008 grams



SOT-23								
Dim	Min	Max						
Α	0.37	0.51						
В	1.20	1.40						
С	2.30	2.50						
D	0.89	1.03						
Е	0.45	0.60						
G	1.78	2.05						
н	2.80	3.00						
J	0.013	0.10						
К	0.903	1.10						
L	0.45	0.61						
М	0.085	0.180						
α	0°	8°						
All Din	nensions	in mm						

Marking Code (Note 2)										
Туре	Marking	Туре	Marking							
BC846A	1A, K1Q	BC847C	1G, K1M							
BC846B	1B, K1R	BC848A	1J, K1J, K1E, K1Q							
BC847A	1E, K1E, K1Q	BC848B	1K, K1K, K1F, K1R							
BC847B	1F, K1F, K1R	BC848C	1L, K1L, K1M							

Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characte	ristic	Symbol	Value	Unit		
Collector-Base Voltage	BC846 BC847 BC848	V _{CBO}	80 50 30	V		
Collector-Emitter Voltage BC846 BC847 BC848		V _{CEO}	65 45 30	V		
Emitter-Base Voltage	BC846, BC847 BC848	V _{EBO}	6.0 5.0	V		
Collector Current		I _C	100	mA		
Peak Collector Current		I _{CM}	200	mA		
Peak Emitter Current		I _{EM}	200	mA		
Power Dissipation (Note 1)		Pd	300	mW		
Thermal Resistance, Junction to Ambient Air (Note 1)		R _{0JA}	417	°C/W		
Operating and Storage Temperatur	e Range	T _j , T _{STG}	-65 to +150	°C		

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout

document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

2. Current gain subgroup "C" is not available for BC846.

3. No purposefully added lead.

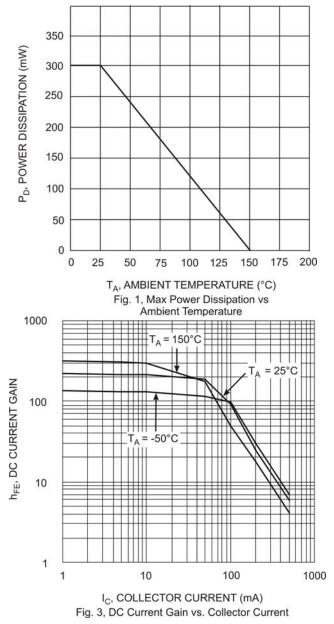


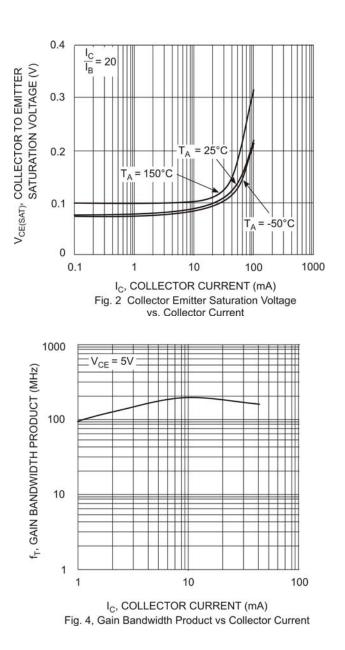
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characterist	tic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage			80		_		
	BC847	V _{(BR)CBO}	50		_	V	$I_{\rm C} = 10 \mu A, I_{\rm B} = 0$
	(BR)0B0	30					
Collector-Emitter Breakdown Voltag		65	_				
	BC847	V _{(BR)CEO}	45	_		V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
	BC848	(811)020	30		_		<i>v y v</i>
Emitter-Base Breakdown Voltage	BC846, BC847	14	6			V	
(Note 3)	BC848	$V_{(BR)EBO}$	5	_	—	v	$I_E = 1\mu A, I_C = 0$
H-Parameters							
Small Signal Current Gain	Current Gain Group A	h _{fe}	_	220			
5	В	h _{fe}	—	330			
	С	h _{fe}	_	600	_	—	
Input Impedance	Current Gain Group A	h _{ie}	—	2.7		kΩ	
	В	h _{ie}	—	4.5	—	kΩ	$V_{CE} = 5.0V, I_{C} = 2.0mA,$
	С	h _{ie}	—	8.7		kΩ	f = 1.0 kHz
Output Admittance	Current Gain Group A	h _{oe}	—	18		μS	
	В	h _{oe}	—	30	—	μS	
	C	h _{oe}	—	60		μS	
Reverse Voltage Transfer Ratio	A	h _{re}	—	1.5x10 ⁻⁴	—		
Current Gain Group	В	h _{re}	—	2×10^{-4}	—		
	C	h _{re}	—	3x10 ⁻⁴	—	—	
DC Current Gain	Current Gain Group A		110	180	220		
	В	h _{FE}	200	290	450	—	$V_{CE} = 5.0V, I_{C} = 2.0mA$
	(Note 4) C		420	520	800		
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	90	250	mV	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA	
	OE(O/(T)		200	600		$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 5.0 {\rm mA}$	
Base-Emitter Saturation Voltage (N	V _{BE(SAT)}	—	700	_	mV	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA	
		DE(GAT)		900			$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 5.0 {\rm mA}$
Base-Emitter Voltage (Note 4)	V _{BE(ON)}	580	660	700	mV	$V_{CE} = 5.0V, I_C = 2.0mA$	
3	500.40	· · · /	_		770		$V_{CE} = 5.0V, I_{C} = 10mA$
Collector-Cutoff Current (Note 4)	BC846	ICES	—	_	15	nA	$V_{CE} = 80V$
	BC847	ICES	_	_	15	nA	$V_{CE} = 50V$
	BC848	CES	_	_	15	nA	$V_{CE} = 30V$
		I _{CBO}	_	_	15 5.0	nA µA	$V_{CB} = 40V$
		I _{CBO}		<u> </u>	5.0	μΑ	$V_{CB} = 30V, T_A = 150^{\circ}C$ $V_{CE} = 5.0V, I_C = 10mA,$
Gain Bandwidth Product		f⊤	100	300		MHz	$v_{CE} = 5.0V, r_{C} = 1000$ f = 1000 Hz
Collector-Base Capacitance		C _{CBO}	_	3.0	_	pF	$V_{CB} = 10V, f = 1.0MHz$
Collector-Dase Capacitatice		CBO		3.0		μ	$V_{CB} = 10V, T = 1.000H2$ $V_{CE} = 5V, I_{C} = 200\mu A,$
Noigo Figuro		NF		2	10	dB	$v_{CE} = 5V, I_C = 200\mu A,$ R _S = 2.0k Ω ,
Noise Figure		INF	_	2	10	uБ	5
							f = 1.0kHz, ∆f = 200Hz

Notes: 4. Short duration pulse test used to minimize self-heating effect.









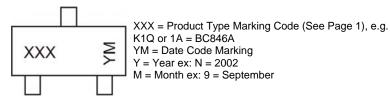
Ordering Information (Note 5)

Device*	Packaging	Shipping
BC84xx-7-F	SOT-23	3000/Tape & Reel

* xx = device type, e.g. BC846A-7-F.

Notes: 5. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	К	L	М	Ν	Р	R	S	Т	U	V	W	Х	Y	Z
Month	Jan	Fe	b I	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t l	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D

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